

6MBI75UA-120



IGBT Module U-Series 1200V / 75A 6 in one-package

■ Features

- High speed switching
- Voltage drive
- Low inductance module structure

■ Applications

- Inverter for Motor drive
- AC and DC Servo drive amplifier
- Uninterruptible power supply
- Industrial machines, such as Welding machines

■ Maximum ratings and characteristics

● Absolute maximum ratings (at Tc=25°C unless otherwise specified)

Item	Symbol	Conditions	Rating	Unit
Collector-Emitter voltage	V _{CES}		1200	V
Gate-Emitter voltage	V _{GES}		±20	V
Collector current	I _C	Continuous	T _C =25°C	A
			T _C =80°C	
	I _{CP}	1ms	T _C =25°C	
			T _C =80°C	
	-I _C		75	
	-I _C pulse		150	
Collector Power Dissipation	P _C	1 device	390	W
Junction temperature	T _J		+150	°C
Storage temperature	T _{stg}		-40 to +125	
Isolation voltage	between terminal and copper base *1	V _{iso}	AC:1min.	VAC
	between thermistor and others *2			
Screw Torque	Mounting *3	-	3.5	N·m

*1 : All terminals should be connected together when isolation test will be done.

*2 : Two thermistor terminals should be connected together, each other terminals should be connected together and shorted to base plate when isolation test will be done.

*3 : Recommendable value : 2.5 to 3.5 N·m(M5)

● Electrical characteristics (at T_J=25°C unless otherwise specified)

Item		Symbols	Conditions		Characteristics			Unit
					Min.	Typ.	Max.	
Inverter	Zero gate voltage collector current	ICES	VGE=0V, VCE=1200V		—	—	1.0	mA
	Gate-Emitter leakage current	IGES	VCE=0V, VGE=±20V		—	—	200	nA
	Gate-Emitter threshold voltage	VGE(th)	VCE=20V, IC=75mA		4.5	6.5	8.5	V
	Collector-Emitter saturation voltage	VCE(sat) (terminal)	VGE=15V, IC=75A	TJ=25°C	—	2.05	2.40	V
				TJ=125°C	—	2.30	—	
		VCE(sat) (chip)		TJ=25°C	—	1.75	2.10	
				TJ=125°C	—	2.00	—	
	Input capacitance	Cies	VCE=10V, VGE=0V, f=1MHz		—	8	—	nF
	Turn-on time	ton	VCC=600V IC=75A VGE=±15V		—	0.25	1.20	μs
		tr			—	0.12	0.60	
		tr(i)			—	0.03	—	
	Turn-off time	toff	RG=9.1 Ω		—	0.36	1.00	
		tf			—	0.07	0.30	
Forward on voltage	VF (terminal)	VGE=0V IF=75A	TJ=25°C	—	2.10	2.50	V	
			TJ=125°C	—	2.30	—		
	VF (chip)		TJ=25°C	—	1.80	2.20		
			TJ=125°C	—	2.00	—		
Reverse recovery time	trr	IF=75A		—	—	0.35	μs	
Lead resistance, terminal-chip*4	R lead			—	4.1	—	mΩ	
Thermistor	Resistance	R	T=25°C	—	5000	—	Ω	
			T=100°C	465	495	520		
	B value	B	T=25/50°C		3305	3375	3450	K

*4:Biggest internal terminal resistance among arm.

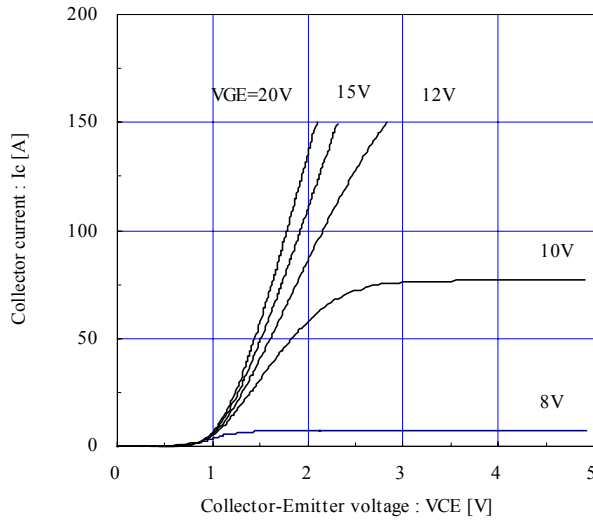
● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Unit
			Min.	Typ.	Max.	
Thermal resistance	R _{th(j-c)}	IGBT	—	—	0.32	°C/W
	R _{th(j-c)}	FWD	—	—	0.73	°C/W
Contact Thermal resistance	R _{th(c-f)} *5	With thermal compound	—	0.05	—	°C/W

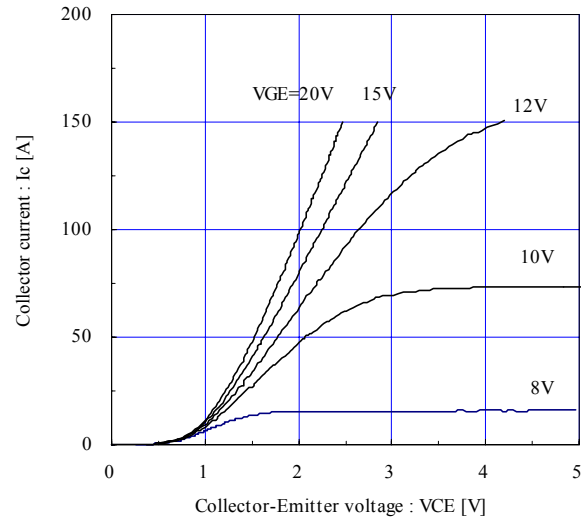
*5 : This is the value which is defined mounting on the additional cooling fin with thermal compound

■ Characteristics (Representative)

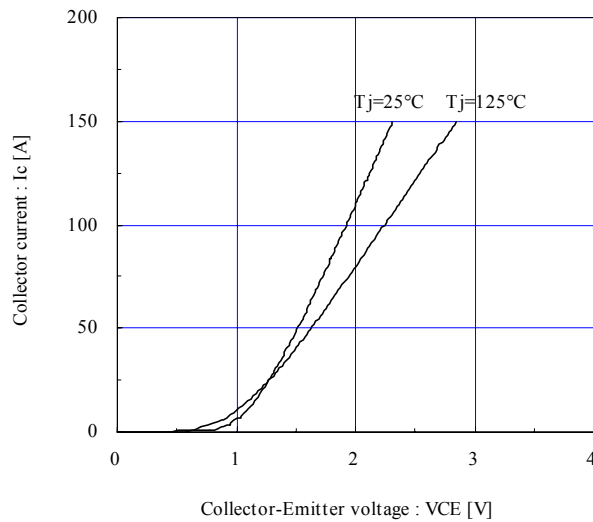
Collector current vs. Collector-Emitter voltage (typ.)

 $T_j = 25^\circ\text{C}$ / chip

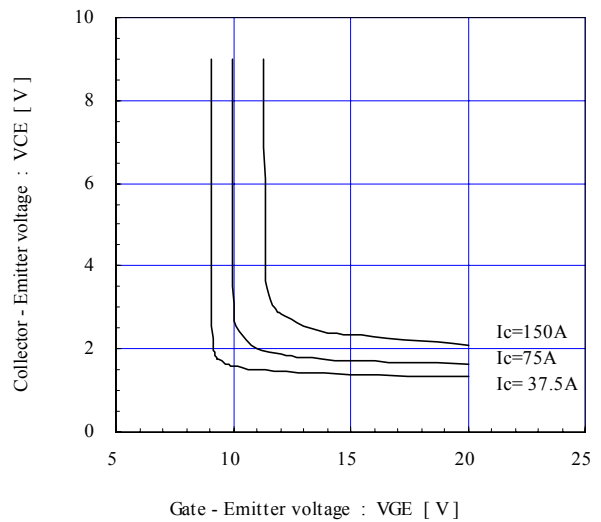
Collector current vs. Collector-Emitter voltage (typ.)

 $T_j = 125^\circ\text{C}$ / chip

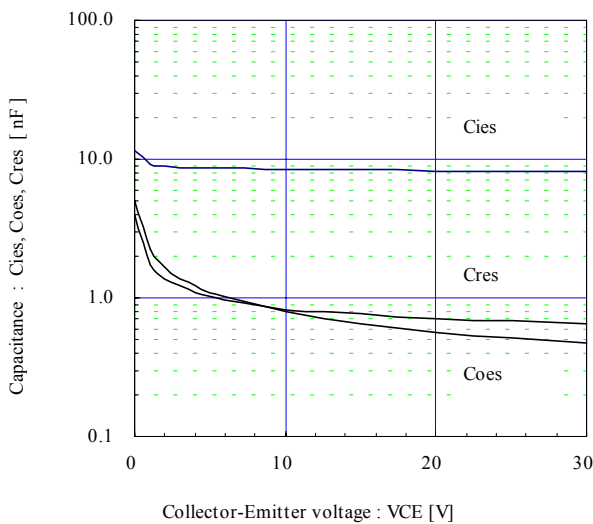
Collector current vs. Collector-Emitter voltage (typ.)

 $V_{GE} = 15\text{V}$ / chip

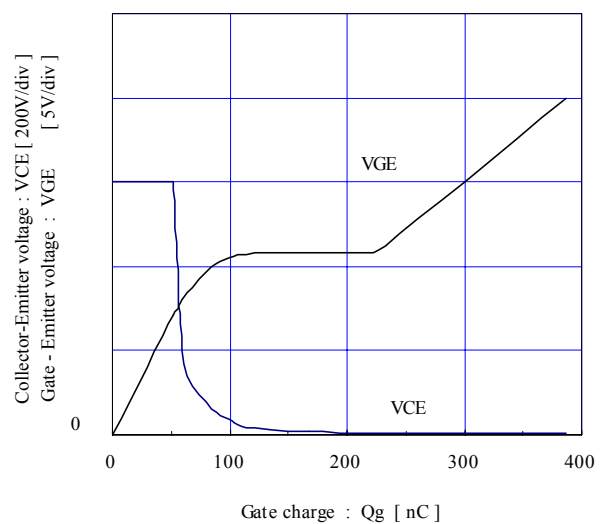
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)

 $T_j = 25^\circ\text{C}$ / chip

Capacitance vs. Collector-Emitter voltage (typ.)

 $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$, $T_j = 25^\circ\text{C}$ 

Dynamic Gate charge (typ.)

 $V_{cc} = 600\text{V}$, $I_c = 75\text{A}$, $T_j = 25^\circ\text{C}$ 

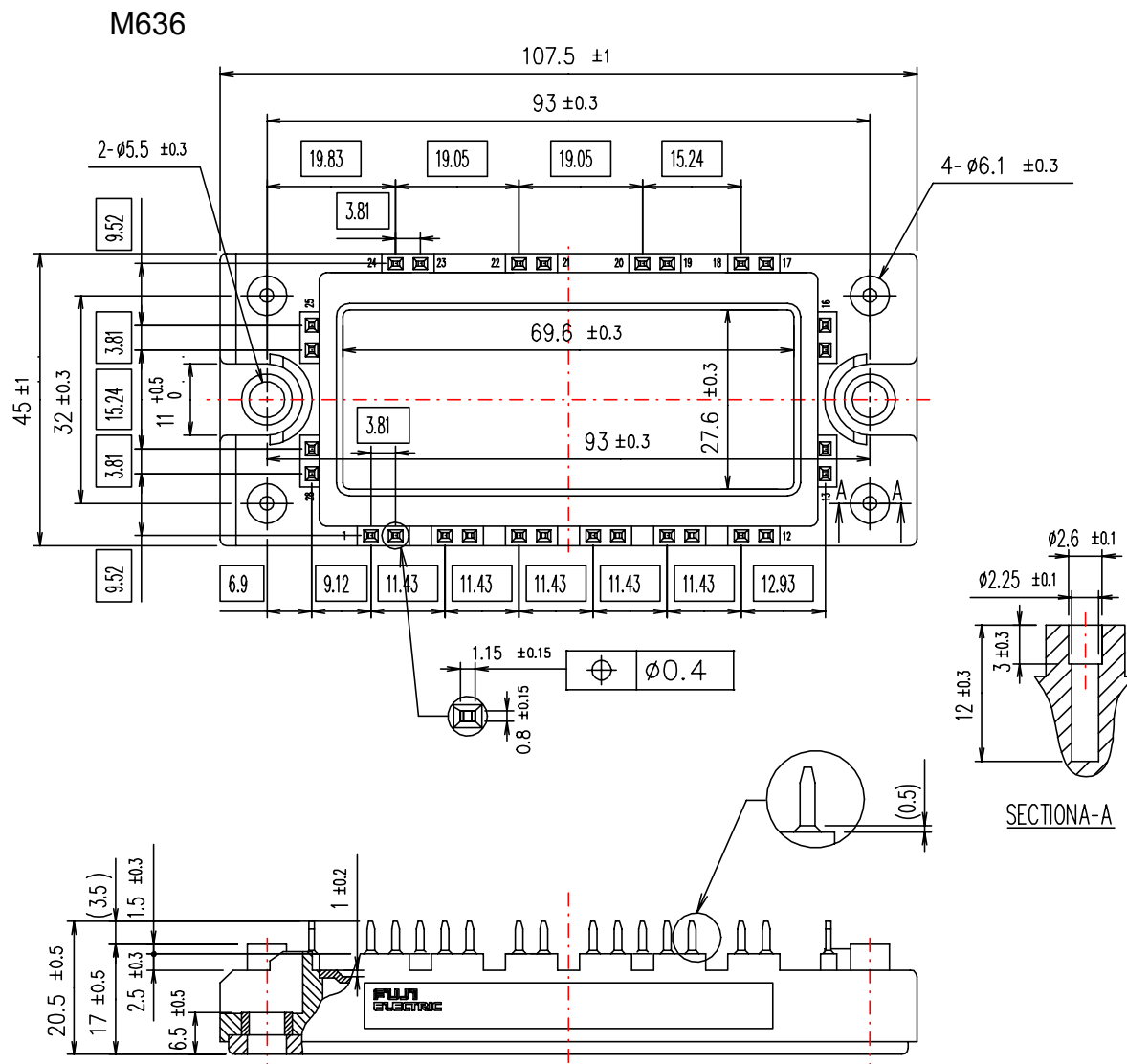
Switching loss vs. Gate resistance (typ.)

+VGE=15V,-VGE ≤ 15V, RG ≥ 9.1

Reverse recovery characteristics (typ.)
V_{cc}=600V, V_{GE}=±15V, R_g=9.1

Transient thermal resistance (max.)

■ Outline Drawings, mm



■ Equivalent Circuit Schematic

